

# RAYCONN ELECTRONICS CO., LTD.

## SPECIFICATION FORM

### FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 25.00MM×19.0MM OUTLINE
- ✧ DUAL DIGIT
- ✧ SINGLE COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

### DESCRIPTION

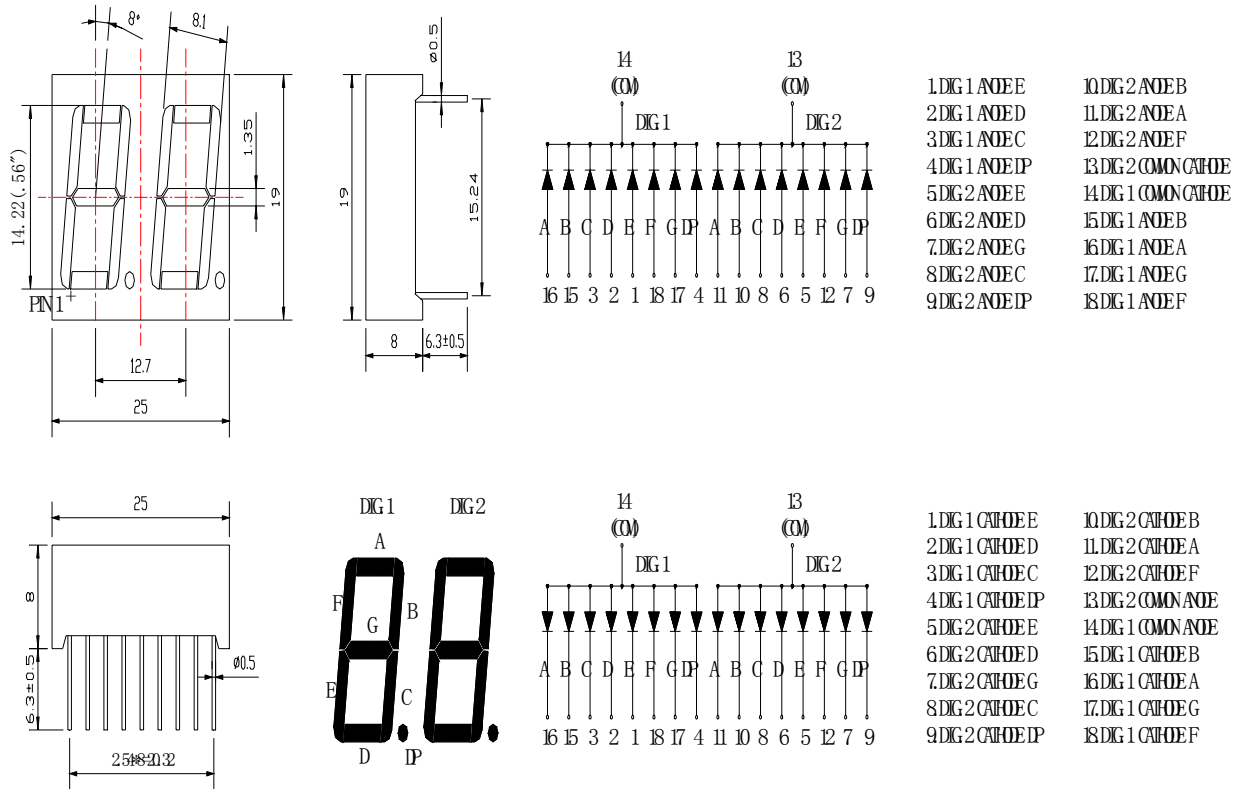
The REC-S5261AG/CG is a 0.56 inches (14.20mm) digit height, 12.6mm×19.0mm outline, single color, dual digit numeric display. This display utilizes green LED chips fabricated from GaP epiwafer on GaP substrate grown by liquid phase epitaxy. These devices have black face and white segments.

### DEVICE

| PART NO.       | EMITTING COLOR | DESCRIPTION                    |
|----------------|----------------|--------------------------------|
| REC-S5261AG/CG | Yellow-Green   | black Face with White Segments |

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## PACKAGE DIMENSION



## ABSOLUTE MAXIMUM RATING AT T<sub>A</sub>=25°C

| PARAMETER                           | SYMBOL          | MAXIMUM | UNIT |
|-------------------------------------|-----------------|---------|------|
| Power Dissipation per Seg.          | P <sub>AD</sub> | 75      | mW   |
| Peak Forward Current per Seg.       | I <sub>PF</sub> | 80      | mA   |
| Continuous Forward Current per Seg. | I <sub>AF</sub> | 20      | mA   |
| Reverse Voltage per Seg.            | V <sub>R</sub>  | 5       | V    |

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|  |                    |
|--|--------------------|
| Operating Temperature Range, $T_{opr}$                                       | - 25° C to + 60° C |
| Storage Temperature Range, $T_{stg}$   | - 30° C to + 85° C |
| Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C |                    |

## ELECTRO – OPTICAL CHARACTERISTICS AT $T_A=25^{\circ}\text{C}$

| PARAMETER  | UNIT          | MIN | TYPE | MAX   |
|--|---------------|-----|------|-------|
| Luminous Intensity per Seg., $I_V$ ( $I_F=20\text{mA}$ )           | mcd           | 10  | 13   | 17    |
| Peak Emission Wavelength, $\lambda_p$ ( $I_F=20\text{mA}$ )        | nm            |     | 570  |       |
| Special Line Half-Width, $\Delta\lambda$ ( $I_F=20\text{mA}$ )     | nm            |     | 30   |       |
| Forward Voltage per Seg., $V_F$ ( $I_F=20\text{mA}$ )              | V             | 2.0 | 2.15 | 2.20  |
| Reverse Current per chipSeg., $I_R$ , ( $V_R=5\text{V}$ )          | $\mu\text{A}$ |     |      | 100   |
| Luminous Intensity Matching Ratio, $I_{V-m}$ ( $I_F=20\text{mA}$ ) |               |     |      | 2 : 1 |